NSN 5962-01-351-4972

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View Online at https://aerobasegroup.com/nsn/5962-01-351-4972			
Overall Length:			
1.280 inches			
Overall Height:			
0.400 inches			
Body Length:			
1.280 inches			
Body Width:			
Between 0.220 inches and 0.310 inches			
Body Height:			
Between 0.140 inches and 0.185 inches			
Maximum Power Dissipation Rating:			
1.2 watts			
Operating Tempurature Range:			
-55.0/+125.0 degrees celsius			
Storage Tempurature Range:			
-65.0/+150.0 degrees celsius			
End Application:			
Satellite communications terminal an/usc-3 (v) 1			
Features Provided:			
High impedance and monolithic and w/clock and bidirectional and bipolar			
Inclosure Material:			
Ceramic			
Inclosure Configuration:			
Dual-in-line Dual-in-line			
Output Logic Form:			
Transistor-transistor logic			
Input Circuit Pattern:			
20 input			
Case Outline Source And Designator:			
D-9 mil-m-38510			
Current Rating Per Characteristic:			
165.00 milliamperes reverse current, dc absolute			
Terminal Surface Treatment:			
Solder			
Product Name:			
And-or invert gate array			
Voltage Rating And Type Per Characteristic:			
-0.5 volts power source and 12.0 volts power source			
Time Rating Per Chacteristic:			
35.00 nanoseconds propagation delay time, high to low level output and 35.00 nanoseconds propagation delay time, low to high level			
output			
Memory Device Type:			

Pal

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Test	Data	Docum	ent
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96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

- i piiilloa oiloa

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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